

DHG10I1200PM

preliminary

 $V_{RRM} = 1200 V$

 $I_{FAV} = 10 A$

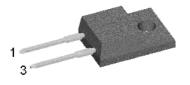
 $t_{rr} = 75 \, \text{ns}$

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Sonic Fast Recovery Diode

Part number

DHG10I1200PM



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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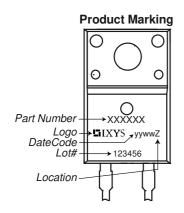
Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
IR	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			15	μΑ
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$			1.2	mΑ
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			2.22	V
		$I_F = 20 A$				2.92	٧
		I _F = 10 A	T _{VJ} = 125°C			2.13	V
		$I_F = 20 A$				3.06	٧
I FAV	average forward current	T _C = 30°C	T _{vJ} = 150°C			10	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{VJ} = 150°C			1.09	٧
\mathbf{r}_{F}	slope resistance	ss calculation only				94	mΩ
R _{thJC}	thermal resistance junction to case)				4	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.5		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			30	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			65	Α
CJ	junction capacitance	$V_R = 600 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		4		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		8		Α
		$I_F = 10 \text{ A}; V_R = 800 \text{ V}$	$T_{VJ} = {}^{\circ}C$		tbd		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 10 \text{ A; } V_R = 800 \text{ V} \\ -di_F /dt = 350 \text{ A/}\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		75		ns
	J		$T_{VJ} = {}^{\circ}C$		tbd		ns



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Package TO-220FP			Rati		5			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					35	Α
T _{VJ}	virtual junction temperature				-55		150	°C
Top	operation temperature				-55		125	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	Ν
d _{Spp/App}	creepage distance on surface striking distance through a	terminal to terminal	3.2	2.7			mm	
$d_{\text{Spb/Apb}}$	creepage distance on surface	e Striking distance through an	terminal to backside	2.5	2.5			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; lisoL ≤ 1 mA		2500			٧
		t = 1 minute			2100			٧



Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

I = Single Diode

1200 = Reverse Voltage [V] PM = TO-220ACFP (2)

Oı	rdering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
St	tandard	DHG10I1200PM	DHG10I1200PM	Tube	50	503672

Similar Part	Package	Voltage class
DHG10I1200PA	TO-220AC (2)	1200

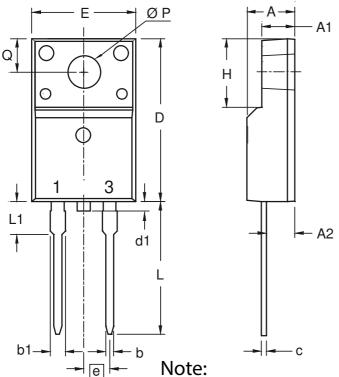
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150$ °C
$I \rightarrow V_0$)—[R ₀]-	Fast Diode		
V _{0 max}	threshold voltage	1.09		V
$R_{0 max}$	slope resistance *	91		$m\Omega$





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Outlines TO-220FP



Dim.	IVIIIIIVI	ieters	inches		
DIIII.	min	max	min	max	
Α	4.50	4.90	0.177	0.193	
A1	2.34	2.74	0.092	0.108	
A2	2.56	2.96	0.101	0.117	
b	0.70	0.90	0.028	0.035	
b1	1.27	1.47	0.050	0.058	
С	0.45	0.60	0.018	0.024	
D	15.67	16.07	0.617	0.633	
d1	0	1.10	0	0.043	
Е	9.96	10.36	0.392	0.408	
е	2.54	BSC	0.100 BSC		
Н	6.48	6.88	0.255	0.271	
L	12.68	13.28	0.499	0.523	
L1	3.03	3.43	0.119	0.135	
ØΡ	3.08	3.28	0.121	0.129	
Q	3.20	3.40	0.126	0.134	

